

PMK35EP

P-channel TrenchMOS extremely low level FET Rev. 02 — 29 April 2010 Pr

Product data sheet

Product profile

1.1 General description

Extremely low level P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

Low conduction losses due to low on-state resistance

1.3 Applications

Battery management

Load switching

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Typ	Mass	1.1 !4
	00.141110110	141111	Тур	wax	Unit
drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	-	-30	V
drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = -10 \text{ V}; \text{ see}$ Figure 1; see Figure 3	-	-	-14. 9	Α
total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	6.9	W
acteristics					
drain-source on-state resistance	$V_{GS} = -10 \text{ V; } I_D = -9.2 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ J}}$	-	16	19	mΩ
naracteristics					
gate-drain charge	$V_{GS} = -10 \text{ V}; I_D = -9.2 \text{ A};$ $V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12	-	6	-	nC
	voltage drain current total power dissipation acteristics drain-source on-state resistance naracteristics	voltage drain current $T_{sp} = 25 ^{\circ}\text{C}; V_{GS} = -10 \text{V}; \text{see}$ Figure 1; see Figure 3 total power dissipation acteristics drain-source $V_{GS} = -10 \text{V}; I_D = -9.2 \text{A};$ on-state $V_{GS} = -10 \text{V}; I_D = -9.2 \text{A};$ resistance paracteristics gate-drain charge $V_{GS} = -10 \text{V}; I_D = -9.2 \text{A};$ $V_{DS} = -15 \text{V}; T_j = 25 ^{\circ}\text{C};$	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	8 <u>7 7 7 7</u> 5	D
3	S	source		
4	G	gate		G $+$ $+$ $+$ $+$ $+$ $+$ $+$ $+$ $+$ $+$
5	D	drain	1	
6	D	drain	SOT96-1 (SO8)	S 001aaa025
7	D	drain		
8	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMK35EP	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	-	-30	V
V_{DGR}	drain-gate voltage	$25 \text{ °C} \le T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	-	-30	V
V_{GS}	gate-source voltage		-25	-	25	V
I _D	drain current	T_{sp} = 25 °C; V_{GS} = -10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	-14.9	А
		T_{sp} = 100 °C; V_{GS} = -10 V; see <u>Figure 1</u>	-	-	-7	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; t_p ≤ 10 μs; pulsed; see Figure 3	-	-	-28.8	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	6.9	W
T _{stg}	storage temperature		-55	-	150	°C
Tj	junction temperature		-55	-	150	°C
Source-drain	n diode					
Is	source current	T _{sp} = 25 °C	-	-	-5.8	Α
I _{SM}	peak source current	T_{sp} = 25 °C; $t_p \le 10 \ \mu s$; pulsed	-	-	-23	Α

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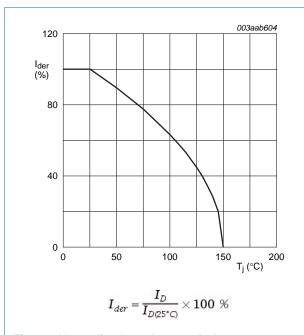


Fig 1. Normalized continuous drain current as a function of solder point temperature

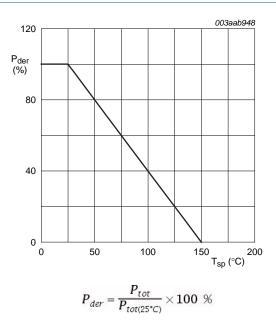


Fig 2. Normalized total power dissipation as a function of solder point temperature

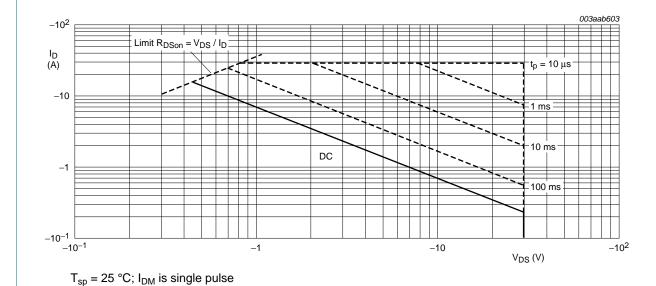


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

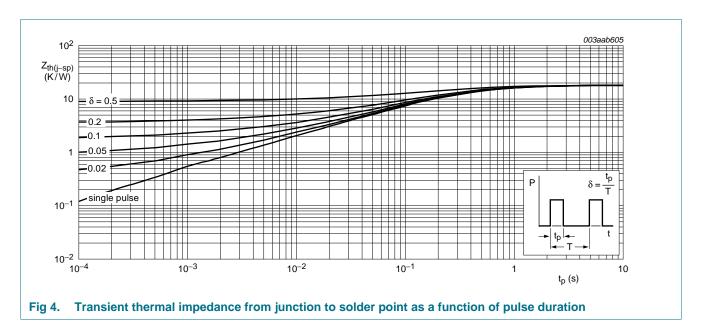
Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point	see <u>Figure 4</u>	-	-	18	K/W

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6. Characteristics

Table 6. Characteristics

	71.41.40.01.101.100					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
	breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	-27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 ^{\circ}\text{C}$; see <u>Figure 8</u>	-1	-	-3	V
	$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 150 ^{\circ}\text{C}$; see <u>Figure 8</u>	-0.7	-	-	V	
		$I_D = -250 \mu A$; $V_{DS} = V_{GS}$; $T_j = -55 ^{\circ}C$; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	-	-3.3	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 70 \text{ °C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_{D} = -9.2 A; T_{j} = 25 °C; see <u>Figure 9</u>	-	16	19	mΩ
		$V_{GS} = -10 \text{ V}; I_D = -9.2 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 9</u>	-	25	31	mΩ
		V_{GS} = -4.5 V; I_D = -6.8 A; T_j = 25 °C; see <u>Figure 10</u> ; see <u>Figure 9</u>	-	26	35	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = -9.2 \text{ A}; V_{DS} = -15 \text{ V}; V_{GS} = -10 \text{ V};$	-	42	-	nC
Q_{GS}	gate-source charge	$T_j = 25 \text{ °C}$; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	8	-	nC
Q_{GD}	gate-drain charge		-	6	-	nC

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Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{GS(pl)}$	gate-source plateau voltage	I_D = -9.2 A; V_{DS} = -15 V; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-2.5	-	V
C _{iss}	input capacitance	$V_{DS} = -25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2100	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 13</u>	-	365	-	pF
C _{rss}	reverse transfer capacitance		-	275	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -25 V; R_L = 6 Ω ; V_{GS} = -10 V;	-	9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	9	-	ns
t _{d(off)}	turn-off delay time		-	50	-	ns
t _f	fall time		-	24	-	ns
Source-drain	n diode					
V_{SD}	source-drain voltage	$I_S = -3.45 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 14	-	-0.8	-1.2	V

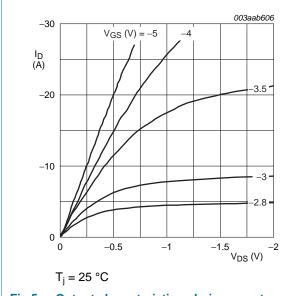


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

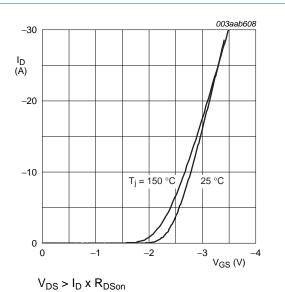


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

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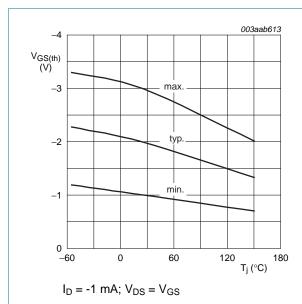
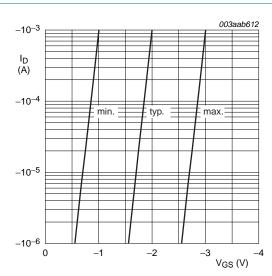


Fig 7. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$

Fig 8. Sub-threshold drain current as a function of gate-source voltage

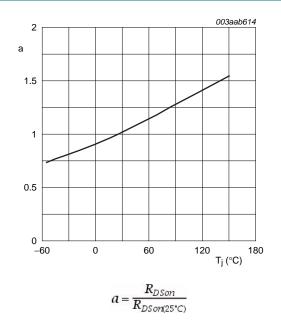


Fig 9. Normalized drain-source on-state resistance factor as a function of junction temperature

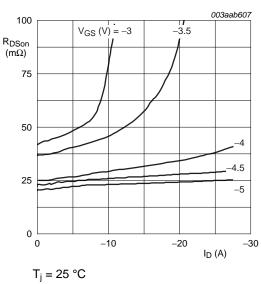


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

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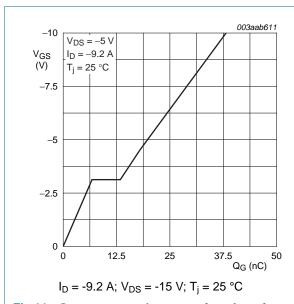


Fig 11. Gate-source voltage as a function of gate charge; typical values

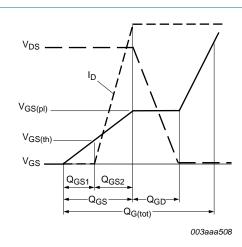


Fig 12. Gate charge waveform definitions

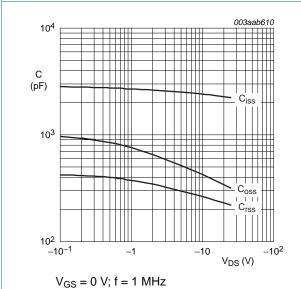


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

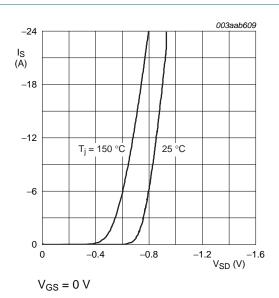


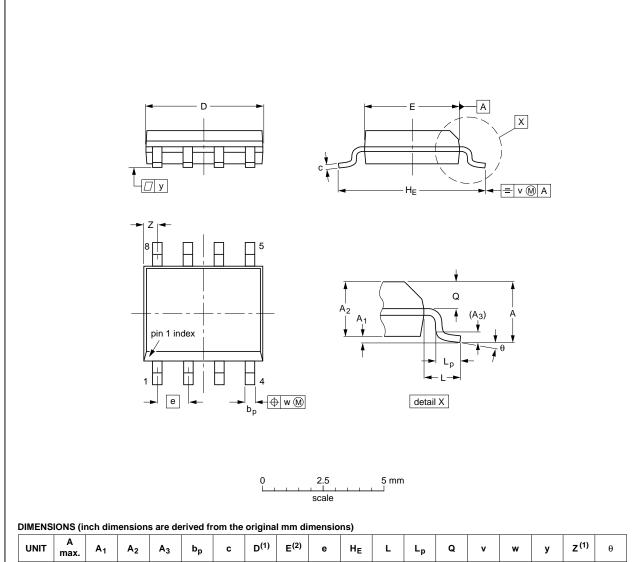
Fig 14. Source current as a function of source-drain voltage; typical values

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7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	σ	٧	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	IEC JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT96-1	076E03	MS-012			99-12-27 03-02-18	

Fig 15. Package outline SOT96-1 (SO8)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMK35EP_2	20100429	Product data sheet	-	PMK35EP_1
Modifications:	 Various cha 	nges to content.		
PMK35EP_1	20070917	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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